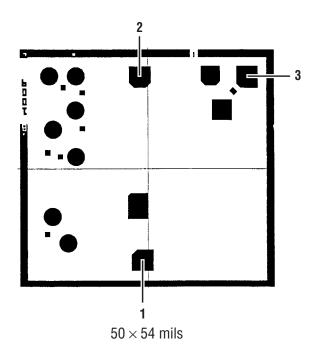


RH1009 2.5V Reference



DIE CROSS REFERENCE

| LTC Finished | Order DICE CANDIDATI | |
|--------------|----------------------|--|
| Part Number | Part Number Below | |
| RH1009 | RH1009 DICE | |
| RH1009 | RH1009 DWF | |

PAD FUNCTION

- 1. V+
- 2. ADJ
- 3. V⁻

NOTE: CONNECT SUBSTRATE TO V-

DICE ELECTRICAL TEST LIMITS

 $T_J = 25^{\circ}C$. Preirradiation

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNITS |
|-------------------------------------|--|--------------------------------|-------|-------|-------|
| V _Z | Reverse Breakdown Voltage | I _R = 1mA | 2.495 | 2.505 | V |
| $\frac{\Delta V_{Z}}{\Delta I_{R}}$ | Reverse Breakdown Voltage Change with Current | 400 μA $\leq I_R \leq 10$ mA | | 6 | mV |

DICE SPECIFICATION

RH1009

Wafer level testing is performed per the indicated specifications for dice. Considerable differences in performance can often be observed for dice versus packaged units due to the influences of packaging and assembly on certain devices and/or parameters. Please consult factory for more information on dice performance and lot qualifications via lot sampling test procedures.

Dice data sheet subject to change. Please consult factory for current revision in production.

I.D.No. 66-13-1009